Mobility effects in polarization switching of lithium niobates

L.-H. Peng, Y.-C. Lin, Y.-C. Fang, Graduate Institute of Electro-Optical Engineering, National Taiwan University, No. 1 Sec. 4, Roosevelt Rd., Taipei 106, Taiwan, ROC; E-mail: peng@cc.ee.ntu.edu.tw

Quasi-phase-matching (QPM) of ferroelectric crystals with periodically 180° inverted domain structures has emerged as an important technology for nonlinear frequency generation. A plethora of research activities on optical parametric and harmonic generation using periodically poled lithium niobate (PPLN) represent one such exciting achievement in nonlinear optics. Great challenge, however, remains in resolving the kinetics of polarization switching such that QPM at a given wavelength can be achieved with an optimum conversion efficiency. In this work, we report a use of transient current analysis to investigate the switching current and switching time on E are due to a field-driven sidewise 180° domain motion. The corresponding equation of motion is characterized by 

\[ v = \mu \left[ E - (E_{\text{int}} \pm E_{\text{out}}) \right], \]

where \( E_{\text{int}} \) and \( E_{\text{out}} \) measure a threshold and internal field strength, respectively, and \( \mu \) a lateral mobility of 1.96 \( \pm 0.05 \) mm²/kV·sec.

The Z-cut, 500 μm-thick LiNbO₃ substrates used in this study were diced into 1 cm × 1 cm squares and had a patterned area of 10 mm² contacted to the lithium chloride (LiCl) liquid electrodes. In order to eliminate the RC charging current and block the charge backflow at the beginning and ending of the poling process, we typically delivered pulses with a baseline field strength greater than 12 kV/mm. By doing so we can ensure a stabilized polarization switching process in LiNbO₃.

In Fig. 1 we illustrate a typical measurement of the switching current during a forward (23.6 kV/mm) and a reverse (22 kV/mm) poling process, respectively. It is found that polarization switching in reverse poling can take place at a smaller field strength (\( E_{s} \)) exhibit a larger switching current (\( i_{s} \)), and substantiate a faster switching time (\( t_{s} \)) compared with the forward poling process. Data shown in Fig. 2 exhibit a linear dependence of \( 1/t_{s} \) and \( i_{s} \) on \( E \), which are independent of the poling direction. These observations represent an apparent sidewise motion of the 180° domain in the high field regime. A mobility model analysis of 

\[ v_{s} = \mu_{s} \left[ E - (E_{\text{in}} \pm E_{\text{out}}) \right], \]

reveals a threshold \( E_{s} \) and internal \( E_{\text{in}} \) field of 17.64 and 3.04 kV/mm, respectively, and \( \mu_{s} \) a lateral mobility of 1.96 \( \pm 0.05 \) mm²/kV·sec.

From the mobility model analysis, the vector sum of \( E \) increases (decreases) the effective field strength in the + reverse (-) poling direction, respectively. It in turn enhances (reduces) the corresponding sidewise velocity \( v_{s} \) and results in the axial anisotropy of sweeping rate (\( 1/t_{s} \)) and switching current (\( i_{s} \)). In applying this method to control the periodical poling process of LiNbO₃, we illustrate in the Fig. 3 an etched y-face of PPLN whose periodicity was designed to be 10 μm. Albeit it is forward poling at a much higher field strength of 23 kV/mm, a good control of the aspect ratio is preserved over the 3 mm sample length and across the 500 μm-thick substrate.

In summary, we report a high field analysis on the kinetics of polarization switching in congruent grown Z-cut LiNbO₃ crystals. The non-stoichiometric point defects introduce an internal field \( E_{\text{int}} \), modify the sidewise 180° domain motion according to 

\[ v = \mu \left[ E - (E_{\text{in}} \pm E_{\text{out}}) \right], \]

and result in an axial anisotropy in the switching current and switching time.

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Laser Displays and Diagnostics

Alan Petersen, Spectral Physics Lasers Inc., USA, Presider

External cancellation of laser FM dither

Matthew Taubmann, John L. Hall, JILA, University of Colorado and NIST, Boulder, Colorado 80309-0440 USA

External laser phase modulation comes with costs, notably Residual Amplitude Modulation (RAM), coherent angle and spatial modulation normally associated with Electro-Optic Modulators. These cause errors in the DC lock point and thus precision limitations. Dither modulation is attractive, being free of these problems. However, a serious signal processing problem arises when characterizing the frequency of highly stable lasers with large dither modulations. With modern random-sampling frequency counters, a completely misleading picture emerges as it reports the large systematic frequency excursions faithfully in its output of the average instantaneous frequency. Older counters may count for a fixed period, 1, 3, or 10 s and so largely suppress these variations. However, the deadtime between counts being not completely stable, a small but similar aliasing problem is still visible over long counting periods, due to shifts between the frequencies of the dither generation and the counter timebase. One can synchronize the various crystal oscillators used in the system, but this gives an unknown frequency shift associated with the start phase. Thus many papers reporting new spectroscopic techniques point out that avoiding Dither locking is preferable. Here we report a demonstrable alternative.

A simple cure for this problem resulting from the laser dither is found by using an